

Silicon Tuning Diode

This device is designed for FM tuning, general frequency control and tuning, or any top-of-the-line application requiring back-to-back diode configurations for minimum signal distortion and detuning.

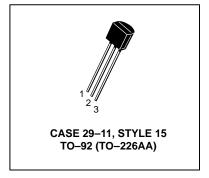
- High Figure of Merit Q = 140 (Typ) @ $V_R = 3.0$ Vdc, f = 100 MHz
- Guaranteed Capacitance Range 37–42 pF @ V_R = 3.0 Vdc (MV104)
- Dual Diodes Save Space and Reduce Cost
- Monolithic Chip Provides Near Perfect Matching Guaranteed ± 1.0% (Max) Over Specified Tuning Range

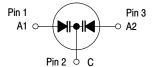
MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	32	Vdc
Forward Current	I _F	200	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	280 2.8	mW mW/°C
Junction Temperature	T _J	+125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

MV104

DUAL VOLTAGE VARIABLE CAPACITANCE DIODE



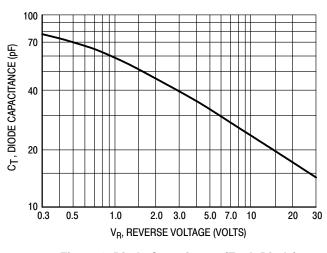


ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (EACH DIODE)

Characteristic		Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μAdc)	V _{(BR)R}	32	_	_	Vdc
Reverse Voltage Leakage Current $T_A = 25$ °C ($V_R = 30 \text{ Vdc}$) $T_A = 60$ °C		_	_	50 500	nAdc
Diode Capacitance Temperature Coefficient (V _R = 4.0 Vdc, f = 1.0 MHz)	TC _C	_	280	_	ppm/°C

	C _T , Diode Capacitance V _R = 3.0 Vdc, f = 1.0 MHz pF		Q, Figure of Merit $V_R = 3.0 \text{ Vdc}$ f = 100 MHz		C_R , Capacitance Ratio C_3/C_{30} f = 1.0 MHz	
Device	Min	Max	Min	Тур	Min	Max
MV104	37	42	100	140	2.5	2.8

TYPICAL CHARACTERISTICS (Each Diode)



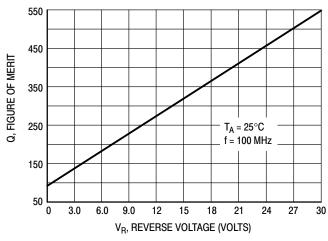
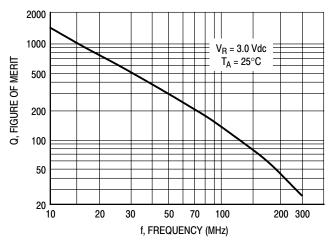


Figure 1. Diode Capacitance (Each Diode)

Figure 2. Figure of Merit versus Voltage



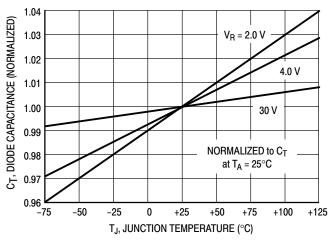


Figure 3. Figure of Merit versus Frequency

Figure 4. Diode Capacitance versus Temperature

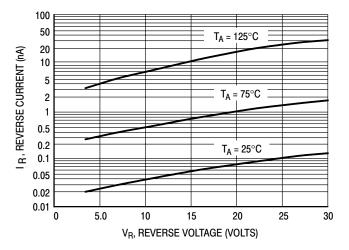
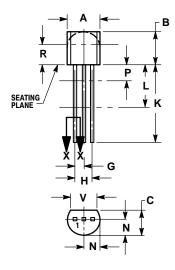


Figure 5. Reverse Current versus Reverse Voltage

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 29-11 ISSUE AL





YLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

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